

10A, 150V, 0.300 Ohm, N-Channel Power MOSFETs

These are N-channel enhancement-mode silicon-gate power field effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA09192.

Ordering Information

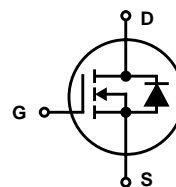
PART NUMBER	PACKAGE	BRAND
RFP10N15	TO-220AB	RFP10N15

NOTE: When ordering, include the entire part number.

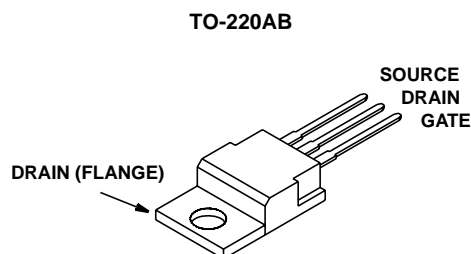
Features

- 10A, 150V
- $r_{DS(ON)} = 0.300\Omega$
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging



RFP10N15

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RFP10N15	UNITS	
Drain to Source Voltage (Note 1)	V_{DS}	150	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR}	150	V
Continuous Drain Current	I_D	10	A
Pulsed Drain Current (Note 3)	I_{DM}	25	A
Gate to Source Voltage	V_{GS}	± 20	V
Maximum Power Dissipation	P_D	60	W
Linear Derating Factor		0.48	W/°C
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	°C
Maximum Temperature for Soldering			
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	°C
Package Body for 10s, See TB334	T_{pkg}	260	°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^\circ\text{C}$ to 125°C .

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}, V_{GS} = 0$	150	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$, (Figure 8)	2	-	4	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = \text{Rated } BV_{DSS}, V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 0.8 \times \text{Rated } BV_{DSS}, T_C = 125^\circ\text{C}$	-	-	25	mA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$	-	-	± 100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 10\text{A}, V_{GS} = 10\text{V}$, (Figures 6, 7)	-	-	0.300	Ω
Drain to Source On Voltage (Note 2)	$V_{DS(ON)}$	$I_D = 10\text{A}, V_{GS} = 10\text{V}$	-	-	3.0	V
Turn-On Delay Time	$t_{d(ON)}$	$I_D \approx 5\text{A}, V_{DD} = 75\text{V}, R_G = 50\Omega$, $V_{GS} = 10\text{V}, R_L = 14.7\Omega$ (Figures 10, 11, 12)	-	40	60	ns
Rise Time	t_r		-	165	250	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	90	135	ns
Fall Time	t_f		-	90	135	ns
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}$, $f = 1\text{MHz}$, (Figure 9)	-	-	850	pF
Output Capacitance	C_{OSS}		-	-	230	pF
Reverse Transfer Capacitance	C_{RSS}		-	-	100	pF
Thermal Resistance Junction to Case		RFP10N15	-	-	2.083	$^\circ\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	$I_{SD} = 5\text{A}$	-	-	1.4	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 4\text{A}, dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	200	-	ns

NOTES:

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
3. Repetitive rating: pulse width is limited by maximum junction temperature.

Typical Performance Curves

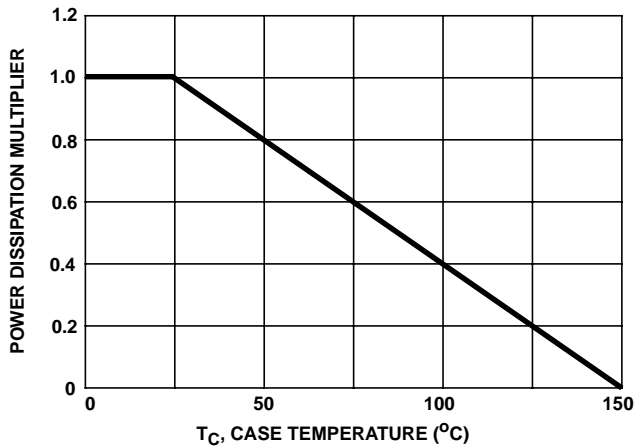


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

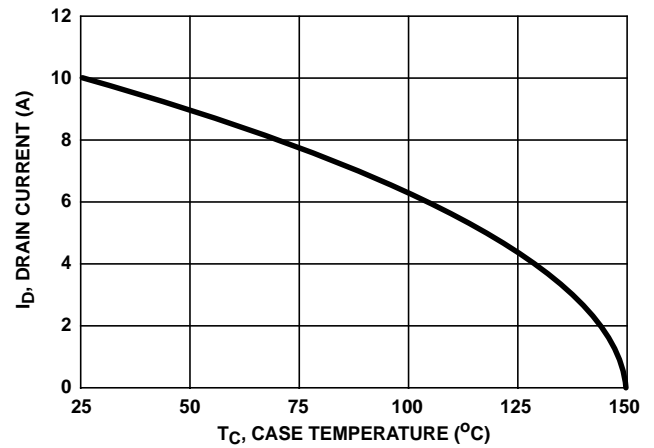


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

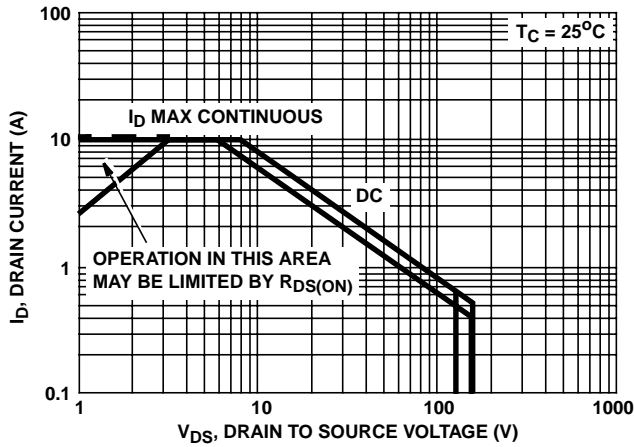


FIGURE 3. FORWARD BIAS SAFE OPERATING AREA

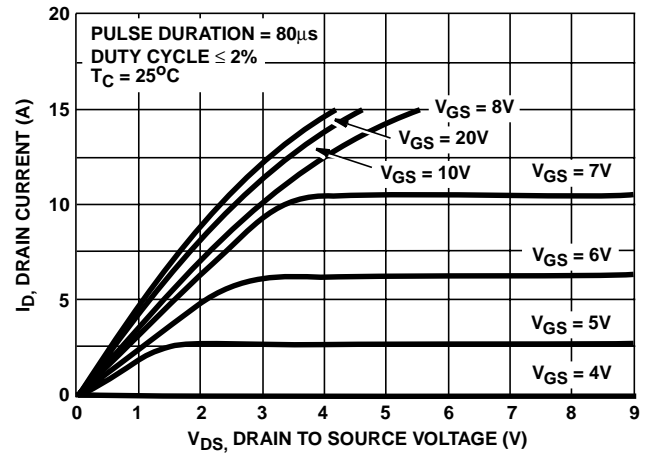


FIGURE 4. SATURATION CHARACTERISTICS

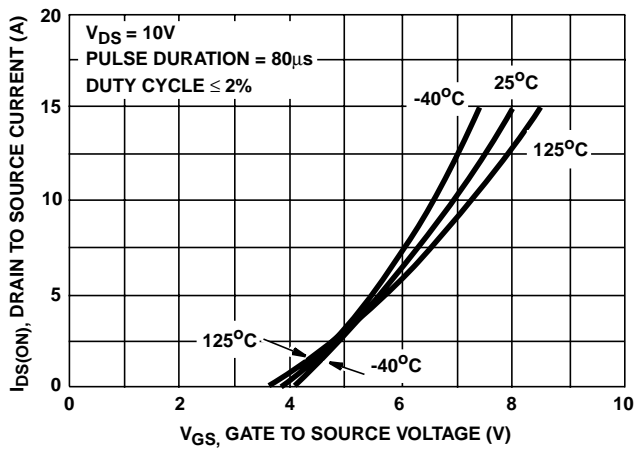


FIGURE 5. TRANSFER CHARACTERISTICS

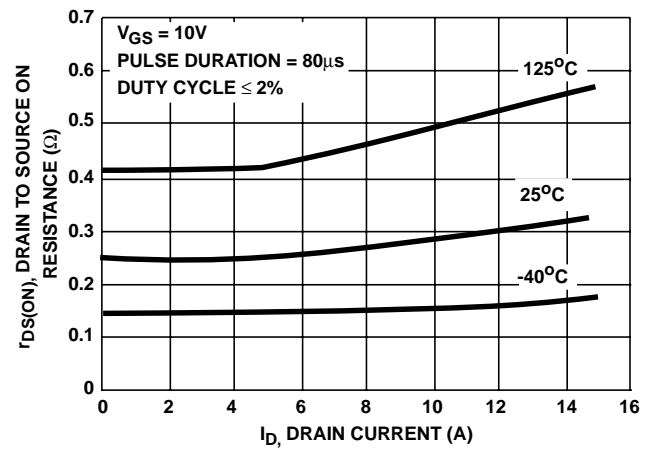


FIGURE 6. DRAIN TO SOURCE ON RESISTANCE vs DRAIN CURRENT